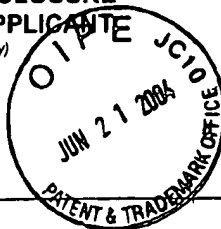


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Application Number	09/944981
Filing Date	August 30, 2001
First Named Inventor	Ahn, Kie
Group Art Unit	2812
Examiner Name	Lindsay, Walter

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Attorney Docket No: 1303.021US1

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WL	US-2003/0052356	03/20/2003	Yang, Haining, et al.	257	309	10/11/2002
WL	US-2003/0052358	03/20/2003	Weimer, Ronald A.	257	310	10/25/2002
WL	US-2003/0102501	06/05/2003	Yang, Haining, et al.	257	295	12/12/2002

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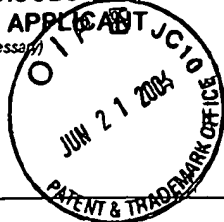
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Application Number 09/944981  
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First Named Inventor Ahn, Kie  
Group Art Unit 2812  
Examiner Name Lindsay, Walter

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CWL	US-2003/0157764	08/21/2003	Ahn, Kie Y., et al.	438	212	02/20/2002
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WL	US-6,025,627	02/15/2000	Forbes, Leonard , et al.	257	321	05/29/1998
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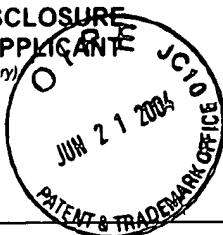
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First Named Inventor Ahn, Kie  
Group Art Unit 2812  
Examiner Name Lindsay, Walter

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WL	US-6,059,885	05/09/2000	Ohashi, Tadashi , et al.	118	730	12/16/1997
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WL	US-6,206,972	03/27/2001	Dunham, Scott W.	118	715	07/08/1999
WL	US-6,207,589	03/27/2001	Ma, Yanjun , et al.	438	785	02/29/2000
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WL	US-6,281,144	08/28/2001	Cleary, Thomas J., et al.	438	780	07/15/1999
WL	US-6,291,866	09/18/2001	Wallace, Robert M., et al.	257	410	10/20/1999
WL	US-6,294,813	09/25/2001	Forbes, Leonard , et al.	257	321	02/15/2000
WL	US-6,297,516	10/02/2001	Forrest, Stephen R., et al.	257	40	06/25/1999
WL	US-6,302,964	10/16/2001	Umotoy, Salvador P., et al.	118	715	03/16/2000
WL	US-6,331,465	12/18/2001	Forbes, Leonard , et al.	438	260	02/15/2000
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WL	US-6,380,579	04/30/2002	Nam, Sang-don , et al.	257	306	04/11/2000
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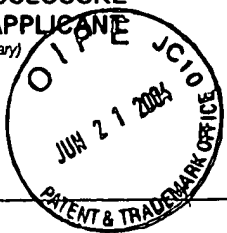
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	Filing Date	August 30, 2001
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	Group Art Unit	2812
	Examiner Name	Lindsay, Walter
Sheet 4 of 12		Attorney Docket No: 1303.021US1



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WL	US-6,448,192	09/10/2002	Kaushik, Vidya S.	438	785	04/16/2001
WL	US-6,451,695	09/17/2002	Sneh, Ofer	438	685	12/22/2000
WL	US-6,455,717	09/24/2002	Vaartstra, Brian A.	556	1	08/28/2000
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WL	US-6,498,063	12/24/2002	Ping, Er-Xuan	438	253	10/12/2001
WL	US-6,514,828	02/04/2003	Ahn, Kie Y., et al.	438	297	04/20/2001
WL	US-6,518,610	02/11/2003	Yang, Haining, et al.	257	295	02/20/2001
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WL	US-6,524,867	02/25/2003	Yang, Haining, et al.	438	3	12/28/2000
WL	US-6,524,901	02/25/2003	Trivedi, Jigish D.	438	183	06/20/2002
WL	US-6,534,420	03/18/2003	Ahn, Kie Y., et al.	438	768	07/18/2001
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WL	US-6,639,267	10/28/2003	Eldridge, Jerome M.	257	310	07/29/2002
WL	US-6,661,058	12/09/2003	Ahn, Kie Y., et al.	257	344	02/11/2002
WL	US-6,682,602	01/27/2004	Vaartstra, Brian A.	118	715	08/19/2002
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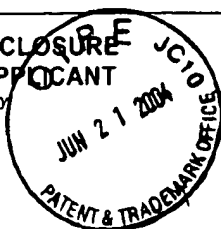
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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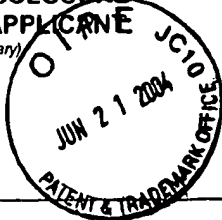
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Examiner Name	Lindsay, Walter

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Attorney Docket No: 1303.021US1

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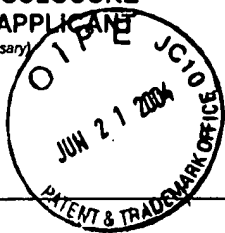
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 Examiner Name Lindsay, Walter

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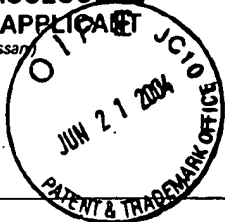
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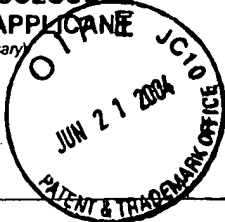
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WL	TAVEL, B , et al., "High performance 40 nm nMOSFETs with HfO/sub 2/ gate dielectric and polysilicon damascene gate", <u>Technical Digest of International Electron Devices Meetings 2002</u> , (2002),429-432	
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